#### DATA SHEET

## NEC

# BIPOLAR ANALOG INTEGRATED CIRCUIT $\mu PC8179TB$

### SILICON MMIC LOW CURRENT AMPLIFIER FOR MOBILE COMMUNICATIONS

#### **DESCRIPTION**

The  $\mu$ PC8179TB is a silicon monolithic integrated circuit designed as amplifier for mobile communications. This IC can realize low current consumption with external chip inductor which can not be realized on internal 50  $\Omega$  wideband matched IC. This low current amplifier operates on 3.0 V.

This IC is manufactured using NEC's 30 GHz f<sub>max</sub> UHS0 (<u>U</u>ltra <u>High Speed Process</u>) silicon bipolar process. This process uses direct silicon nitride passivation film and gold electrodes. These materials can protect the chip surface from pollution and prevent corrosion/migration. Thus, this IC has excellent performance, uniformity and reliability.

#### **FEATURES**

Low current consumption : Icc = 4.0 mA TYP. @ Vcc = 3.0 V

Supply voltage : Vcc = 2.4 to 3.3 V

• High efficiency : Po (1 dB) = +3.0 dBm TYP. @ f = 1.0 GHz

Po (1 dB) = +1.5 dBm TYP. @ f = 1.9 GHzPo (1 dB) = +1.0 dBm TYP. @ f = 2.4 GHz

Power gain : G<sub>P</sub> = 13.5 dB TYP. @ f = 1.0 GHz

G<sub>P</sub> = 15.5 dB TYP. @ f = 1.9 GHz G<sub>P</sub> = 15.5 dB TYP. @ f = 2.4 GHz

• Excellent isolation : ISL = 44 dB TYP. @ f = 1.0 GHz

ISL = 42 dB TYP. @ f = 1.9 GHz ISL = 41 dB TYP. @ f = 2.4 GHz

• Operating frequency : 0.1 to 2.4 GHz (Output port LC matching)

• High-density surface mounting : 6-pin super minimold package  $(2.0 \times 1.25 \times 0.9 \text{ mm})$ 

Light weight : 7 mg (Standard value)

#### **APPLICATION**

Buffer amplifiers on 0.1 to 2.4 GHz mobile communications system

Caution Electro-static sensitive devices

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

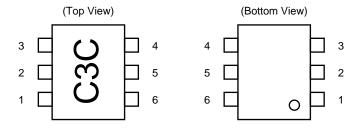


#### ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
μPC8179TB-E3	6-pin super minimold	C3C	Embossed tape 8 mm wide.  1, 2, 3 pins face the perforation side of the tape.  Qty 3 kpcs/reel.

**Remark** To order evaluation samples, please contact your local NEC sales office. (Part number for sample order:  $\mu$ PC8179TB)

#### **PIN CONNECTIONS**



Pin No.	Pin Name			
1	INPUT			
2	GND			
3	GND			
4	OUTPUT			
5	GND			
6	Vcc			



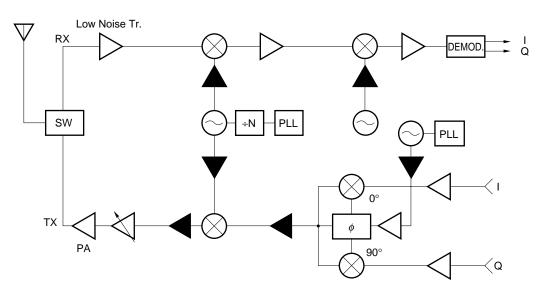
#### PRODUCT LINE-UP (TA = +25 °C, Vcc = Vout = 3.0 V, Zs = ZL = 50 $\Omega$ )

Parameter			1.0 GHz output port matching frequency		1.66 GHz output port matching frequency		1.9 GHz output port matching frequency		2.4 GHz output port matching frequency			Marking		
Part No.	Icc (mA)	G <sub>P</sub> (dB)	ISL (dB)	P <sub>O(1 dB)</sub> (dBm)	G <sub>P</sub> (dB)	ISL (dB)	P <sub>O(1 dB)</sub> (dBm)	G <sub>P</sub> (dB)	ISL (dB)	P <sub>O(1 dB)</sub> (dBm)	G <sub>P</sub> (dB)	ISL (dB)	P <sub>O(1 dB)</sub> (dBm)	
μPC8178TB	1.9	11	39	-4.0	_	_	_	11.5	40	-7.0	11.5	38	-7.5	СЗВ
μPC8179TB	4.0	13.5	44	+3.0	I	ı	-	15.5	42	+1.5	15.5	41	+1.0	C3C
μPC8128TB	2.8	12.5	39	-4.0	13	39	-4.0	13	37	-4.0	1	Í	_	C2P
μPC8151TB	4.2	12.5	38	+2.5	15	36	+1.5	15	34	+0.5	ı	İ	_	C2U
μPC8152TB	5.6	23	40	-4.5	19.5	38	-8.5	17.5	35	-8.5	1		_	C2V

Remark Typical performance. Please refer to ELECTRICAL CHARACTERISTICS in detail.

#### SYSTEM APPLICATION EXAMPLE

Location examples in digital cellular



These ICs can be added to your system around ▲ parts, when you need more isolation or gain. The application herein, however, shows only examples, therefore the application can depend on your kit evaluation.

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#### PIN EXPLANATION

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V) <sup>Note</sup>	Function and Applications	Internal Equivalent Circuit
1	INPUT	-	1.09	Signal input pin. A internal matching circuit, configured with resisters, enables 50 $\Omega$ connection over a wide band. This pin must be coupled to signal source with capacitor for DC cut.	
2 3 5	GND	0	_	Ground pin. This pin should be connected to system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible.  All the ground pins must be connected together with wide ground pattern to decrease impedance defference.	6 4
4	ОИТРИТ	voltage as same as Vcc through external inductor	-	Signal output pin. This pin is designed as collector output. Due to the high impedance output, this pin should be externally equipped with LC matching circuit to next stage. For L, a size 1005 chip inductor can be chosen.	3 1 5
6	Vcc	2.4 to 3.3	-	Power supply pin. This pin should be externally equipped with bypass capacitor to minimize its impedance.	

**Note** Pin voltage is measured at Vcc = 3.0 V.



#### **ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	Vcc	T <sub>A</sub> = +25 °C, Pin 4, Pin 6	3.6	V
Circuit Current	Icc	T <sub>A</sub> = +25 °C	15	mA
Power Dissipation	P <sub>D</sub>	Mounted on double sided copper clad $50 \times 50 \times 1.6$ mm epoxy glass PWB (T <sub>A</sub> = +85 °C)	270	mW
Operating Ambient Temperature	TA		-40 to +85	°C
Storage Temperature	Tstg		-55 to +150	°C
Input Power	Pin	T <sub>A</sub> = +25 °C	+5	dBm

#### **RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Remarks
Supply Voltage	Vcc	2.4	3.0	3.3	V	The same voltage should be applied to pin 4 and pin 6.
Operating Ambient Temperature	TA	-40	+25	+85	°C	

#### **ELECTRICAL CHARACTERISTICS**

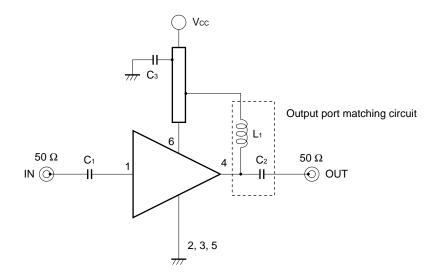
(Unless otherwise specified,  $T_A = +25$  °C,  $V_{CC} = V_{out} = 3.0$  V,  $Z_S = Z_L = 50$   $\Omega$ , at LC matched frequency)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	Icc	No signal	2.9	4.0	5.4	mA
Power Gain	G₽	f = 1.0 GHz, P <sub>in</sub> = -30 dBm f = 1.9 GHz, P <sub>in</sub> = -30 dBm f = 2.4 GHz, P <sub>in</sub> = -30 dBm	11.0 13.0 13.0	13.5 15.5 15.5	15.5 17.5 17.5	dB
Isolation	ISL	$f = 1.0 \text{ GHz}, P_{in} = -30 \text{ dBm}$ $f = 1.9 \text{ GHz}, P_{in} = -30 \text{ dBm}$ $f = 2.4 \text{ GHz}, P_{in} = -30 \text{ dBm}$	39 37 36	44 42 41	- - -	dB
1 dB Gain Compression Output Power	Po(1dB)	f = 1.0 GHz f = 1.9 GHz f = 2.4 GHz	-0.5 -2.0 -3.0	+3.0 +1.5 +1.0	- - -	dBm
Noise Figure	NF	f = 1.0 GHz f = 1.9 GHz f = 2.4 GHz	- - -	5.0 5.0 5.0	6.5 6.5 6.5	dB
Input Return Loss (Without matching circuit)	RLin	f = 1.0 GHz, P <sub>in</sub> = -30 dBm f = 1.9 GHz, P <sub>in</sub> = -30 dBm f = 2.4 GHz, P <sub>in</sub> = -30 dBm	4 4 6	7 7 9	- - -	dB

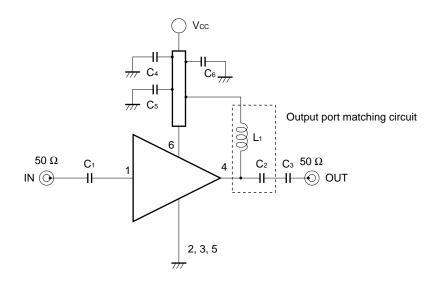
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#### **TEST CIRCUITS**

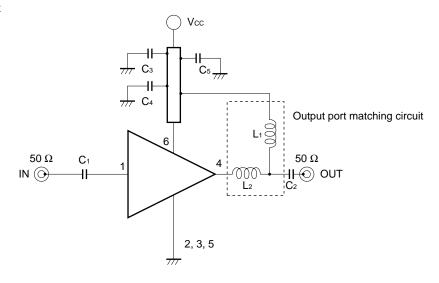
<1> f = 1.0 GHz



<2> f = 1.9 GHz



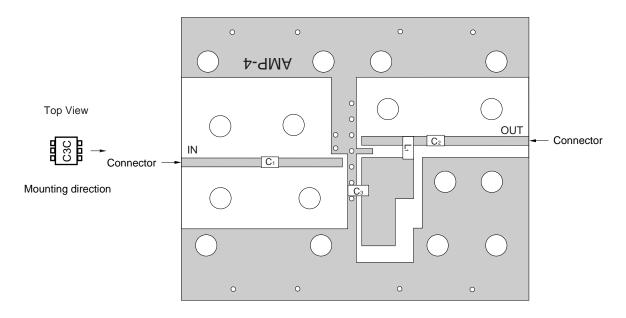
<3> f = 2.4 GHz





#### ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD

<1> f = 1.0 GHz

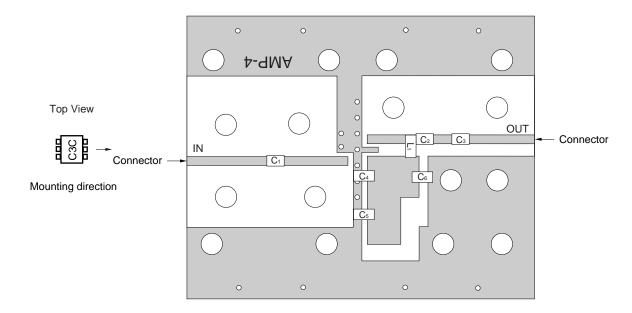


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#### **COMPONENT LIST**

	1.0 GHz Output Port Matching
C <sub>1</sub>	1 000 pF
C <sub>2</sub>	0.75 pF
<b>C</b> <sub>3</sub>	10 pF
L <sub>1</sub>	12 nH

#### <2> f = 1.9 GHz

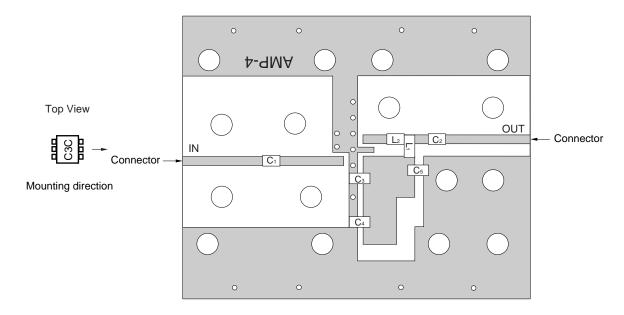


#### COMPONENT LIST

	1.9 GHz Output Port Matching
C1, C3, C5, C6	1 000 pF
C <sub>2</sub>	0.75 pF
C <sub>4</sub>	10 pF
L <sub>1</sub>	3.3 nH



<3> f = 2.4 GHz



#### **COMPONENT LIST**

2.4 GHz Output Port Matchir				
C1, C2, C4, C5	1 000 pF			
<b>C</b> 3	10 pF			
L <sub>1</sub>	1.8 nH			
L <sub>2</sub>	2.7 nH			

#### **NOTES**

(\*1)  $42 \times 35 \times 0.4$  mm double sided copper clad polyimide board

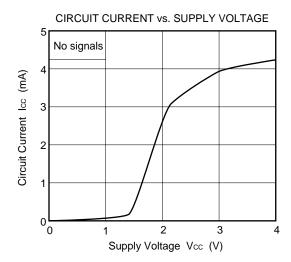
(\*2) Solder plated on pattern

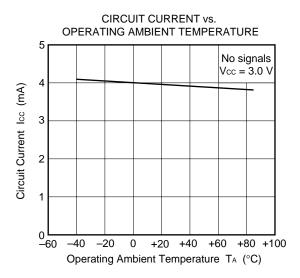
(\*3) Back side: GND pattern

(∗4) ○ ○: Through holes

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#### TYPICAL CHARACTERISTICS (unless otherwise specified, TA = +25°C)

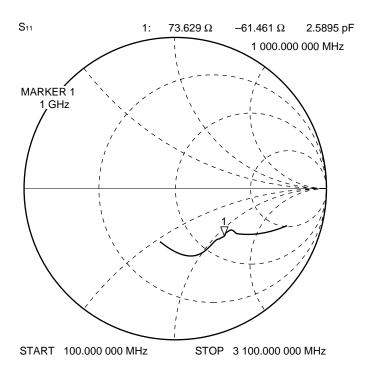


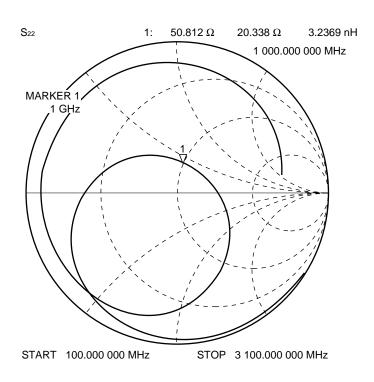


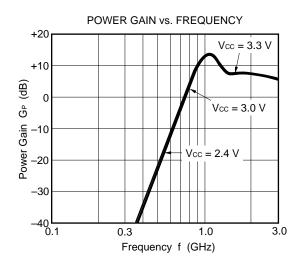


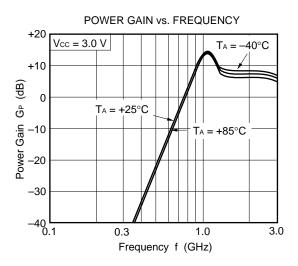
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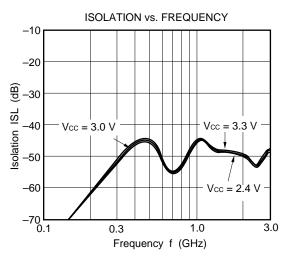
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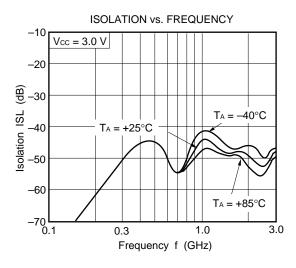


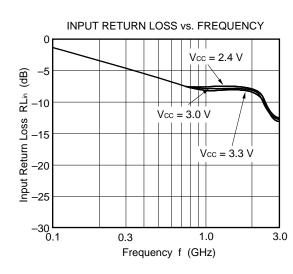


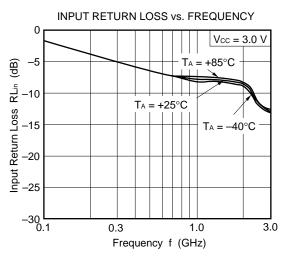




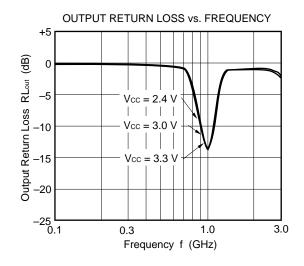


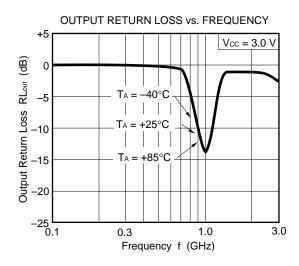


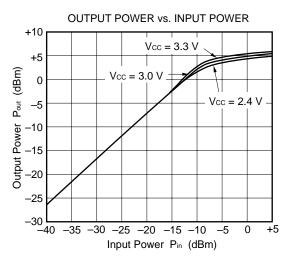


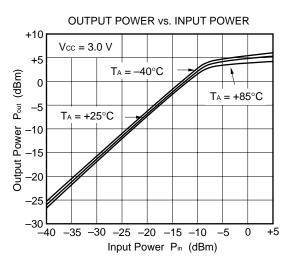


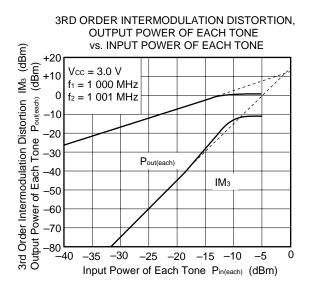


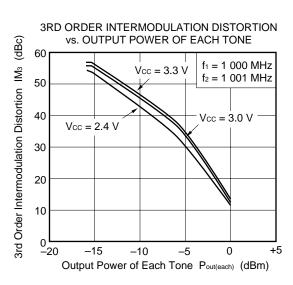


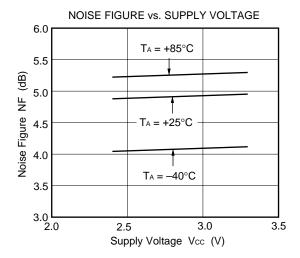








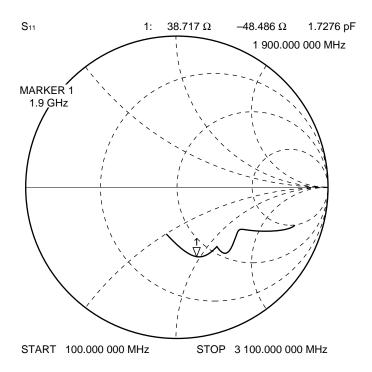


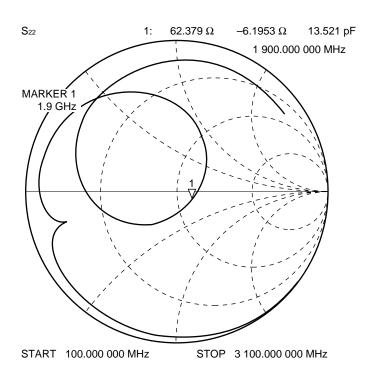


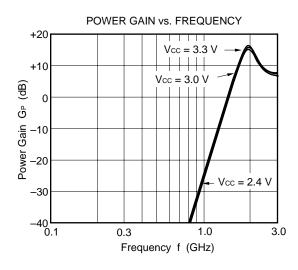


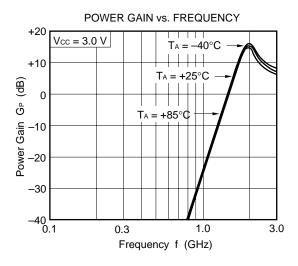
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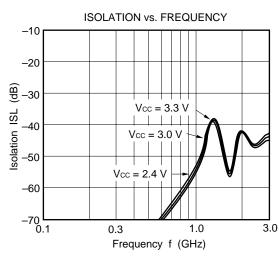
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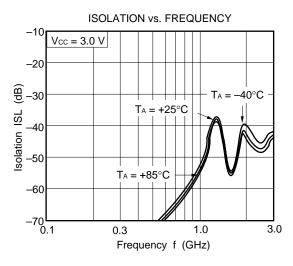


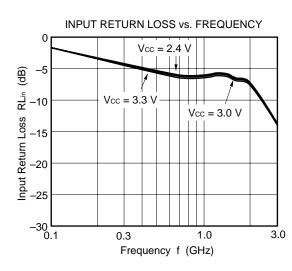


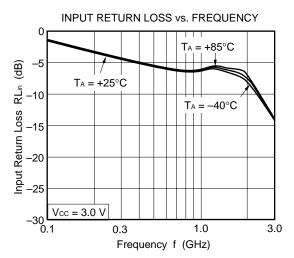




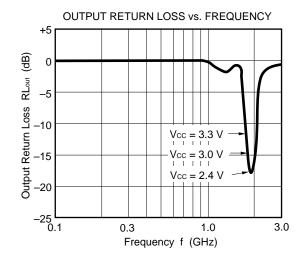


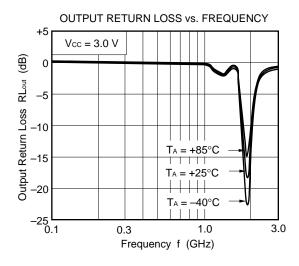


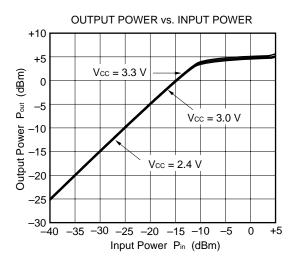


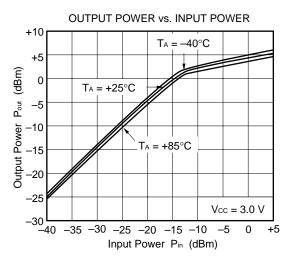


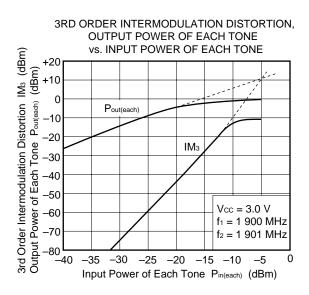


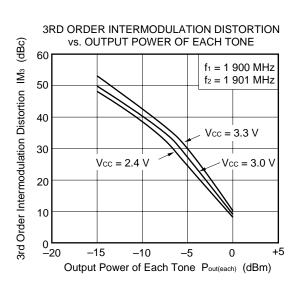


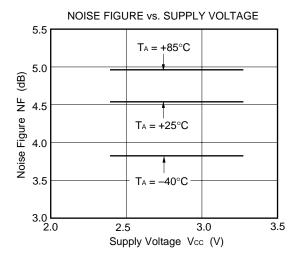








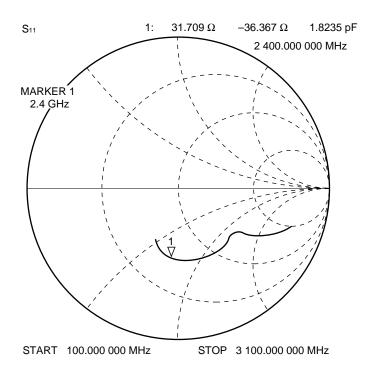


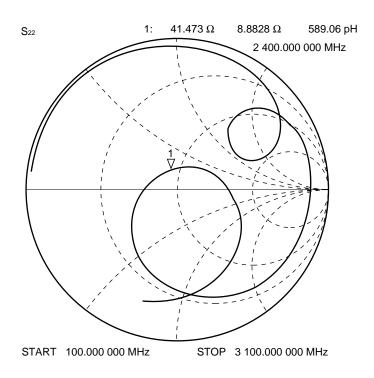


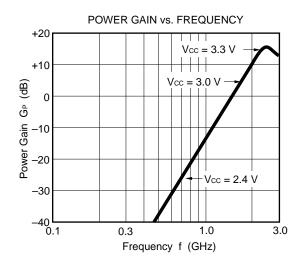


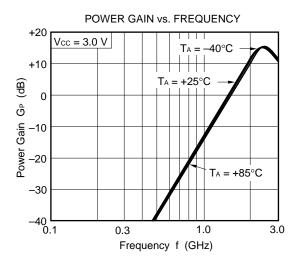
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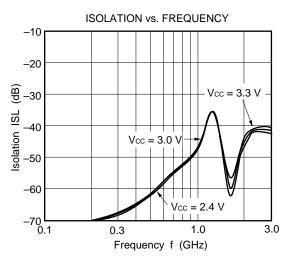
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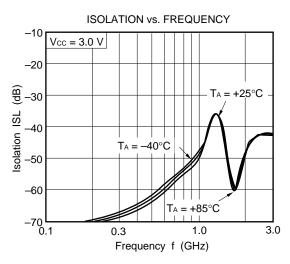


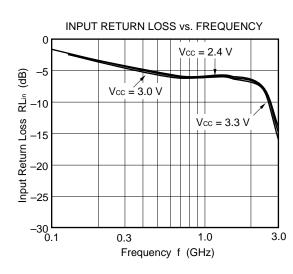


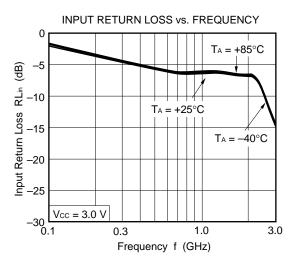




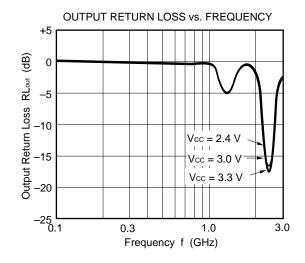


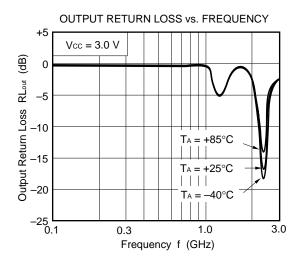


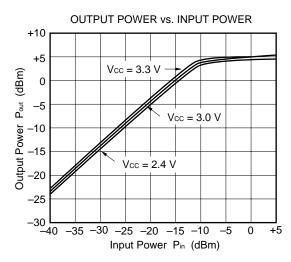


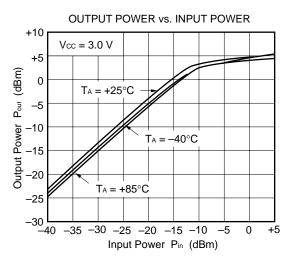


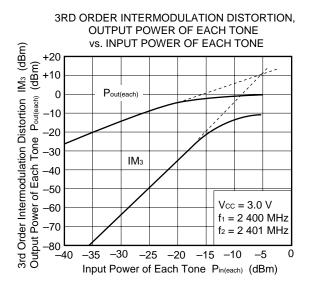


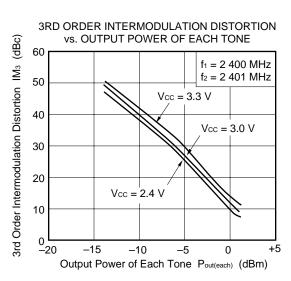


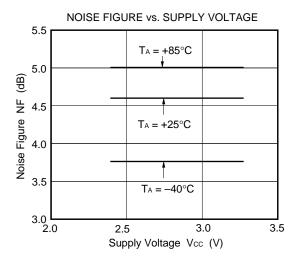










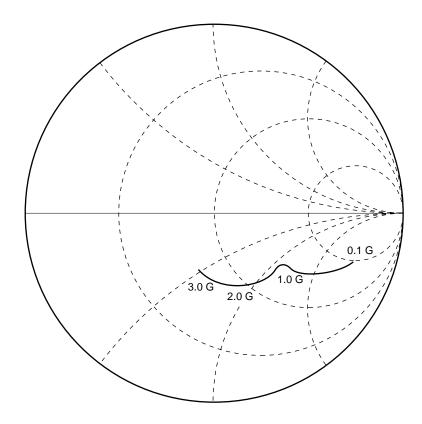


**Remark** The graphs indicate nominal characteristics.

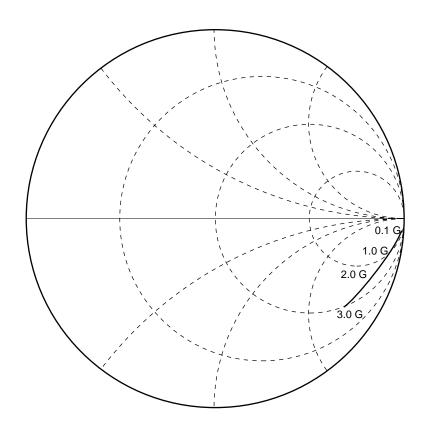


#### S-PARAMETER (Vcc = Vout = 3.0 V)

#### S<sub>11</sub>-FREQUENCY



#### S<sub>22</sub>-FREQUENCY



#### TYPICAL S-PARAMETER VALUES (TA = +25°C)

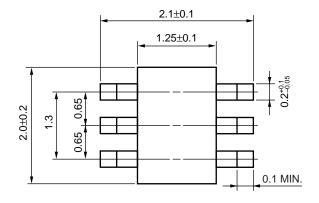
Vcc = Vout = 3.0 V, Icc = 4.0 mA

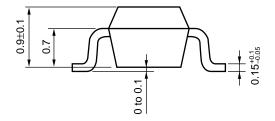
FREQUENCY	S	511	S	<b>S</b> 21	S	12	S	22
MHz	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
100.0000	0.824	-17.1	1.181	-177.7	0.002	108.8	0.996	-2.4
200.0000	0.692	-25.9	1.181	-172.4	0.003	64.7	0.986	-4.0
300.0000	0.594	-29.2	1.247	-167.4	0.004	51.3	0.980	-5.8
400.0000	0.533	-30.7	1.370	-164.1	0.005	55.8	0.965	-7.5
500.0000	0.499	-31.1	1.514	-162.4	0.005	60.6	0.958	-8.6
600.0000	0.474	-32.0	1.677	-162.9	0.006	46.6	0.950	-10.1
700.0000	0.460	-32.7	1.885	-163.8	0.006	42.9	0.941	-11.2
800.0000	0.450	-34.0	2.050	-166.3	0.006	45.9	0.935	-12.4
900.0000	0.441	-35.6	2.237	-169.2	0.005	42.1	0.929	-13.8
1000.0000	0.438	-37.7	2.460	-173.1	0.007	34.0	0.918	-14.9
1100.0000	0.431	-39.8	2.627	-177.3	0.007	46.9	0.914	-16.0
1200.0000	0.426	-42.0	2.772	178.4	0.005	27.7	0.903	-17.0
1300.0000	0.427	-44.8	2.965	173.2	0.005	40.2	0.895	-18.3
1400.0000	0.417	-48.1	3.123	168.0	0.004	24.4	0.891	-19.5
1500.0000	0.413	-50.6	3.199	161.8	0.006	45.5	0.884	-20.4
1600.0000	0.408	-54.6	3.351	156.8	0.005	44.6	0.877	-21.1
1700.0000	0.398	-57.6	3.345	151.2	0.003	42.4	0.867	-22.1
1800.0000	0.387	-61.6	3.403	145.5	0.005	42.7	0.861	-23.0
1900.0000	0.380	-64.9	3.361	140.9	0.005	59.5	0.859	-24.4
2000.0000	0.366	-69.1	3.375	136.3	0.004	45.4	0.852	-25.1
2100.0000	0.352	-72.1	3.350	132.3	0.003	58.3	0.846	-25.9
2200.0000	0.341	-75.6	3.304	127.9	0.003	73.9	0.847	-26.4
2300.0000	0.330	-79.4	3.347	124.8	0.006	81.1	0.839	-27.4
2400.0000	0.320	-82.4	3.325	121.2	0.006	98.3	0.839	-28.2
2500.0000	0.304	-85.6	3.275	117.3	0.006	100.5	0.838	-29.1
2600.0000	0.296	-88.2	3.284	113.7	0.004	114.6	0.834	-29.7
2700.0000	0.285	-91.7	3.283	111.0	0.005	104.8	0.830	-30.6
2800.0000	0.272	-94.3	3.224	106.5	0.005	114.1	0.831	-31.4
2900.0000	0.267	-96.9	3.333	104.3	0.008	127.8	0.837	-32.0
3000.0000	0.256	-99.5	3.251	101.1	0.009	126.3	0.831	-33.4
3100.0000	0.248	-101.9	3.381	96.0	0.008	134.1	0.833	-34.0



#### PACKAGE DIMENSIONS

#### 6 PIN SUPER MINIMOLD (UNIT: mm)







#### NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation).

  All the ground pins must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to Vcc line.
- (4) The inductor (L) should be attached between output and Vcc pins. The L and series capacitor (C) values should be adjusted for applied frequency to match impedance to next stage.
- (5) The DC capacitor must be attached to input pin.

#### RECOMMENDED SOLDERING CONDITIONS

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared Reflow	Package peak temperature: 235°C or below Time: 30 seconds or less (at 210°C) Count: 3, Exposure limit: None <sup>Note</sup>	IR35-00-3
VPS	Package peak temperature: 215°C or below Time: 40 seconds or less (at 200°C) Count: 3, Exposure limit: None <sup>Note</sup>	VP15-00-3
Wave Soldering	Soldering bath temperature: 260°C or below Time: 10 seconds or less Count: 1, Exposure limit: None <sup>Note</sup>	WS60-00-1
Partial Heating	Pin temperature: 300°C Time: 3 seconds or less (per side of device) Exposure limit: None <sup>Note</sup>	-

Note After opening the dry pack, keep it in a place below 25°C and 65% RH for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

For details of recommended soldering conditions for surface mounting, refer to information document **SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E)**.

[MEMO]





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